WNSC6D10650X



Silicon Carbide Diode

Rev.01 - 11 August 2022

Product data sheet

1. General description

Silicon Carbide Schottky diode in a TO220F-2L plastic package, designed for high frequency switched-mode power supplies.



2. Features and benefits

- New 6th Generation Technology
- Low Forward Voltage Drop
- Low Reverse Leakage Current
- High Forward Surge Capability I_{FSM}
- Reduced losses in associated MOSFET
- Reduced EMI
- Reduced cooling requirements
- RoHS compliant

3. Applications

- Power factor correction
- Telecom / Server SMPS
- UPS
- PV inverter
- PC Silverbox
- LED / OLED TV
- Motor Drives

4. Quick reference data

Table 1. Q	uick reference data						
Symbol	Parameter	Conditions	Notes	Values			Unit
Absolute	maximum rating						
V_{RRM}	repetitive peak reverse voltage				650		V
$I_{F(AV)}$	average forward current	δ = 0.5 ; square-wave pulse; T _h ≤ 96 °C; Fig. 1; Fig. 2; Fig. 3			10		A
Tj	junction temperature			-	55 to 17	5	°C
Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
Static ch	aracteristics						
V _F	forward voltage	I _F = 10 A; T _j = 25 °C; <u>Fig. 5</u>		-	1.29	1.45	V
		I _F = 10 A; T _j = 150 °C; <u>Fig. 5</u>		-	1.45	1.65	V
		I _F = 10 A; T _j = 175 °C; <u>Fig. 5</u>		-	1.50	1.70	V

5. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode		K IA A
2	А	anode	oOo	K <u>– K</u> 001aaa020
mb	n.c.	mounting base; isolated		

6. Ordering information

Table 3. Ordering information								
Type number	Package name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date		
WNSC6D10650X	TO220F-2L	WNSC6D10650X6Q	Tube	50	TO220FN-2L	20-July-2016		

7. Marking

Table 4. Marking codes	
Type number	Marking codes
WNSC6D10650X	WNSC6D 10650X

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Notes	Values	Unit
V _{RRM}	repetitive peak reverse voltage			650	V
V _{RWM}	crest working reverse voltage			650	V
V _R	reverse voltage	DC		650	V
I _{F(AV)}	average forward current	δ = 0.5; square-wave pulse; T _h ≤ 96 °C; Fig. 1; Fig. 2; Fig. 3		10	A
I _{FRM}	repetitive peak forward current	δ = 0.5; t _p = 25 µs; T _h ≤ 96 °C; square-wave pulse		20	A
I _{FSM}	non-repetitive peak	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse		75	А
	forward current	$t_p = 10 \ \mu s; T_{j(init)} = 25 \ ^{\circ}C; square-wave pulse$		800	А
l ² t	I ² t for fusing	t _p = 10 ms; T _{j(init)} = 25 °C; sine-wave pulse		28	A ² s
T _{stg}	storage temperature			-55 to 175	°C
Tj	junction temperature			-55 to 175	°C

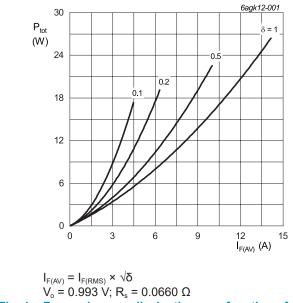
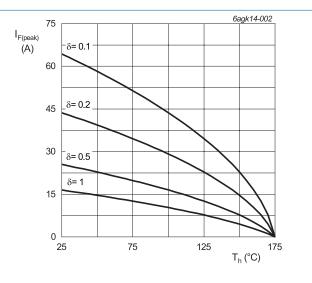
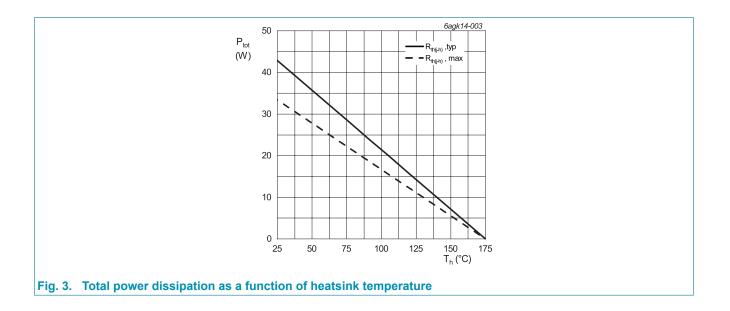


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values



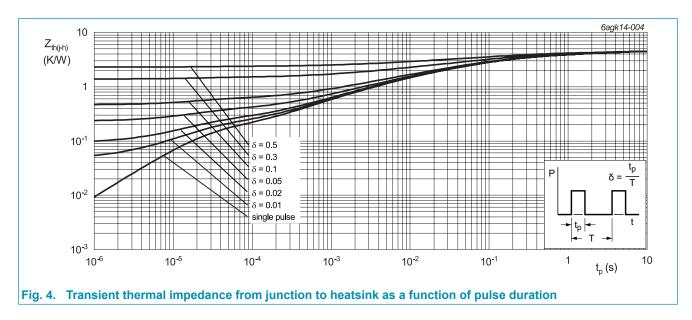


WNSC6D10650X Silicon Carbide Diode



9. Thermal characteristics

Table 6. Th	ermal characteristics						
Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
$R_{th(j-h)}$	thermal resistance from junction to heatsink	with heatsink compound; Fig. 4		-	3.5	4.5	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	in free air		-	60	-	K/W

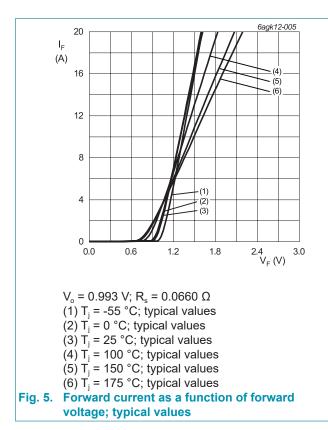


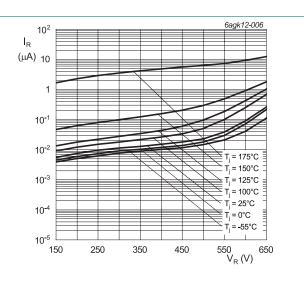
10. Isolation characteristics

Fable 7. Isolation characteristics							
Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
V _{isol(RMS)}	RMS isolation voltage	from all terminals to external heatsink; sinusoidal waveform; clean and dust free; 50 Hz \leq f \leq 60 Hz; T _h = 25 °C; RH \leq 65 %		-	-	2500	V

11. Characteristics

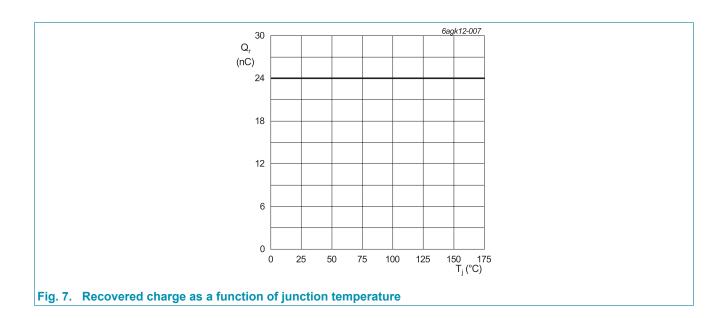
Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
	racteristics						
V _F	forward voltage	I _F = 10 A; T _j = 25 °C; <u>Fig. 5</u>		-	1.29	1.45	V
		I _F = 10 A; T _j = 150 °C; <u>Fig. 5</u>		-	1.45	1.65	V
		I _F = 10 A; T _j = 175 °C; <u>Fig. 5</u>		-	1.50	1.70	V
I _R	reverse current	V _R = 650 V; T _j = 25 °C; <u>Fig. 6</u>		-	1	50	μA
		V _R = 650 V; T _j = 175 °C; <u>Fig. 6</u>		-	15	200	μA
Dynamic	characteristics			,			
Q _r	recovered charge	$I_F = 10 \text{ A}; V_R = 400 \text{ V}; \text{ d}_F/\text{d}t = 500 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$		-	24	-	nC
C _d	diode capacitance	f = 1 MHz; V _R = 1 V; T _j = 25 °C		-	500	-	pF
		f = 1 MHz; V _R = 300 V; T _j = 25 °C		-	58	-	pF
		f = 1 MHz; V _R = 600 V; T _j = 25 °C		-	52	-	pF
E _{as}	non-repetitive avalanche energy	I _R = 5 A; T _{j(init)} = 25 °C; L = 5 mH		60	-	-	mJ



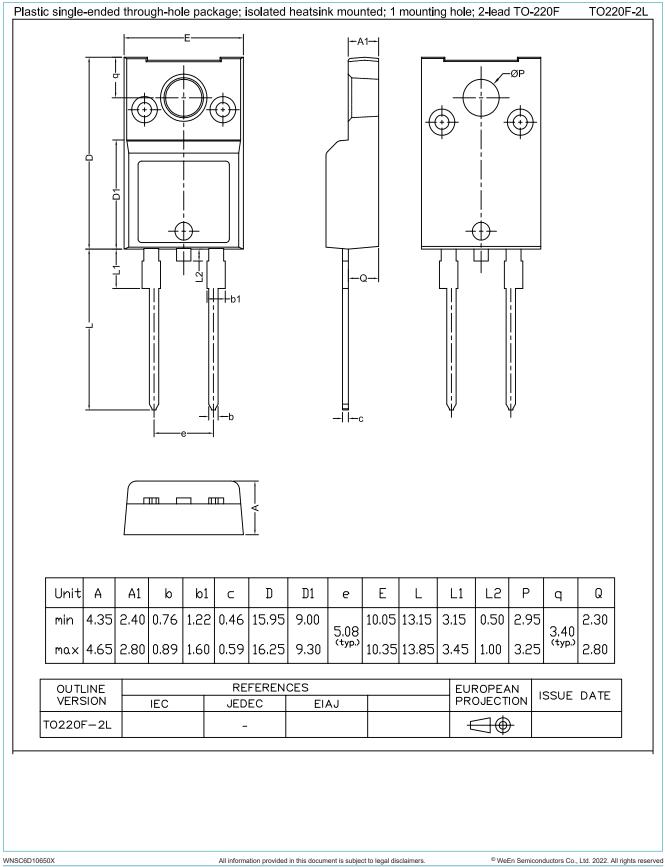




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12. Package outline



WNSC6D10650X

Silicon Carbide Diode

13. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

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